Product Overview

NSS12100M3: Low $V_{CE(sat)}$ Transistor, PNP, 12 V, 1.0 A

For complete documentation, see the data sheet.

Low VCE(sat) Bipolar Transistors are miniature surface mount devices featuring ultra low saturation voltage VCE(sat) and high current gain capability. These are designed for use in low voltage, high speed switching applications where affordable efficient energy control is important.

Features

- High Continuous Current Capability
- Low VCE(sat) (typically 150mV at 500mA)
- Small Size 1.2 mm x 1.2 mm
- This is a Pb-Free Device

Benefits

- High Specific Current and Power Cabability Reduces Required PCB area
- Reduced Parasitic Losses Increases Battery Life

Applications

- Load Switching, Battery Charging, External Pass Transistor, DC/DC Converter, Complimentary Driver, Current Extention & Low Drop Out Regulation, Cathode Florescent Lamp drive, Peripheral Driver - LEDs, Motors, Relays

End Products

- Mobile phones
- Digital Camera
- PDA

Part Electrical Specifications

Product	Pricing ($/Unit)	Compliance	Status	Polarity	Type	$V_{CE(sat)}$ Max (V)	I_C Cont. (A)	V_{CEO} Min (V)	V_{CBO} (V)	V_{EBO} (V)	$V_{BE(sat)}$ (V)	$V_{BE(on)}$ (V)	h_{FE} Min	h_{FE} Max	f_T Min (MHz)	P_{TM} Max (W)	Package Type
NSS12100M3T5G	0.1501	Pb-free Halide free	Active	PNP	Low $V_{CE(sat)}$	0.06	1	12	12	5	1.15	1.2	120	-	-	0.48	SOT-723-3

For more information please contact your local sales support at www.onsemi.com.

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